



## 74AUP2G126 DUAL 3-STATE BUFFER

## Description

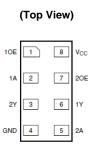
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G126 is a dual 3-State Buffer. Each buffer has an individual output enable pin while asserted LOW will place the output in a high impedance state. The device is designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

### Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption
- I<sub>CC</sub> < 0.9μA
- Low Dynamic Power Consumption
- C<sub>PD</sub> = 6pF Typical at 3.6V
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250mV at V<sub>CC</sub> = 3.0V
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection per JESD 22
  - Exceeds 200-V Machine Model (A115)
  - Exceeds 2000-V Human Body Model (A114)
  - Exceeds 1000-V Charged Device Model (C101)
  - Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages per JESD30E
  - DFN1210 Denoted as X2-DFN1210-8
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Pin Assignments**



X2-DFN1210-8

## Applications

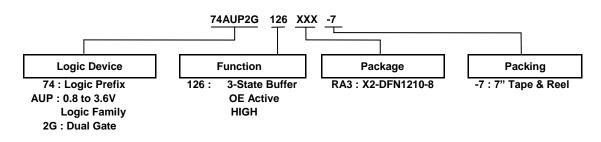
- Suited for Battery and Low Power Needs
- Wide Array of Products Such as:
  - Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 Players, Cameras, Video Recorders
  - PCs, Ultrabooks, Notebooks, Netbooks
  - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
  - TV, DVD, DVR, Set-Top Box

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



## **Ordering Information**



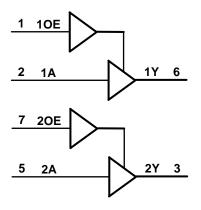
Device	Package	Package	Package	7" Tape and Reel			
Device	Code (Notes 4, 5) Size		Quantity	Part Number Suffix			
74AUP2G126RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3mm Lead Pitch	5000/Tape & Reel	-7		

 Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf
The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf Notes:

## **Pin Descriptions**

Pin NO.	Pin Name	Description
1	10E	Output Enable Active HIGH
2	1A	Data Input
3	2Y	Data Output
4	GND	Ground
5	2A	Data Input
6	1Y	Data Output
7	20E	Output Enable Active HIGH
8	Vcc	Supply Voltage

## Logic Diagram



## **Function Table**

Inpu	Output	
OE	А	Y
Н	Н	Н
Н	L	L
L	Х	Z



## Absolute Maximum Ratings (Notes 6, 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current (VI < 0)	50	mA
I <sub>OK</sub>	Output Clamp Current (V <sub>O</sub> < 0)	50	mA
lo	Continuous Output Current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
Icc	Continuous Current Through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

## Recommended Operating Conditions (Note 8)

Symbol	Para	ameter	Min	Max	Unit
Vcc	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
		$V_{CC} = 0.8V$	—	-20	μA
		$V_{CC} = 1.1V$	—	-1.1	
	Lligh Lough Output Current	$V_{CC} = 1.4V$	—	-1.7	
Іон	High-Level Output Current	V <sub>CC</sub> = 1.65V	—	-1.9	mA
		$V_{CC} = 2.3V$	—	-3.1	
		$V_{CC} = 3.0V$	—	-4	
		$V_{CC} = 0.8V$	—	20	μA
		$V_{CC} = 1.1V$	—	1.1	
		$V_{CC} = 1.4V$	—	1.7	
I <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 1.65V	—	1.9	mA
		V <sub>CC</sub> = 2.3V	—	3.1	
		V <sub>CC</sub> = 3.0V	—	4	
Δt/ΔV	Input Transition Rise or Fall Rate V <sub>CC</sub> = 0.8V to 3.6V		—	200	ns/V
T <sub>A</sub>	Operating Free-Air Temperature	•	-40	+125	°C

Note: 8. Unused inputs should be held at  $V_{CC}$  or Ground.



## **Electrical Characteristics**

Symbol	nbol Parameter	Test Conditions	V	T <sub>A</sub> = -	+25°C	T <sub>A</sub> = -40°0	C to +85°C	Unit	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit	
		—	0.8V to 1.65V	0.80 X V <sub>CC</sub>	—	0.80 X V <sub>CC</sub>	_		
VIH	High-Level Input	—	1.65V to 1.95V	0.65 X V <sub>CC</sub>	_	$0.65 \text{ X V}_{\text{CC}}$	_	V	
VIH	Voltage	—	2.3V to 2.7V	1.6		1.6	—	v	
		—	3.0V to 3.6V	2.0	_	2.0	—		
		—	0.8V to 1.65V	—	0.30 X V <sub>CC</sub>	—	$0.30 \text{ X} \text{ V}_{\text{CC}}$		
VIL	Low-Level Input	—	1.65V to 1.95V	—	0.35 X V <sub>CC</sub>	—	$0.35 \text{ X} \text{ V}_{\text{CC}}$	V	
۷IL	Voltage	—	2.3V to 2.7V	—	0.7	—	0.7	v	
		—	3.0V to 3.6V		0.9	—	0.9		
		I <sub>OH</sub> = -20µА	0.8V to 3.6V	V <sub>CC</sub> - 0.1	—	Vcc-0.1	—		
		I <sub>OH</sub> = -1.1mA	1.1V	$0.75 \text{ X V}_{CC}$	—	0.7 X V <sub>CC</sub>	—		
	High-Level Output Voн Voltage	I <sub>OH</sub> = -1.7mA	1.4V	1.11	—	1.03	—		
		I <sub>OH</sub> = -1.9mA	1.65V	1.32		1.3	—		
VOH		I <sub>OH</sub> = -2.3mA	2.01/	2.05	_	1.97	_	V	
		I <sub>OH</sub> = -3.1mA	2.3V	1.9	_	1.85	_		
		I <sub>OH</sub> = -2.7mA		2.72	_	2.67	_		
		$I_{OH} = -4mA$	3V	2.6	_	2.55	_		
		I <sub>OL</sub> = 20μA	0.8V to 3.6V	_	0.1	_	0.1		
		$I_{OL} = 1.1 \text{mA}$	1.1V		0.3 X V <sub>CC</sub>	_	0.3 X V <sub>CC</sub>		
		$I_{OL} = 1.7 \text{mA}$	1.4V	_	0.31	_	0.37	V	
	Low-Level Output	$I_{OL} = 1.9 \text{mA}$	1.65V	_	0.31	_	0.35		
Vol	Voltage	$I_{OL} = 2.3 \text{mA}$			0.31	_	0.33		
		$I_{OL} = 3.1 \text{mA}$	2.3V		0.44		0.45		
		$I_{OL} = 2.7 \text{mA}$		_	0.31	_	0.33		
		$I_{OL} = 4mA$	3V		0.44	_	0.45		
		A or B Input			0.11		0.10		
h	Input Current	$V_1 = GND \text{ to } 3.6V$	0 to 3.6V	—	±0.1	—	±0.5	μA	
I <sub>OZ</sub>	Z-State Leakage Current	$V_{\rm I}$ or $V_{\rm O} = 0V$ to 3.6V	0 to 3.6V	_	0.2	—	±0.5	μA	
IOFF	Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V	_	±0.2	_	±0.5	μA	
$\Delta I_{OFF}$	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	0.2	_	0.6	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA	
		Data Input at						•	
		V <sub>CC</sub> -0.6V	3.3V	_	40	_	50	μA	
		$OE = GND, I_O = 0A$							
	ΔI <sub>CC</sub> Additional Supply Current C	OE Input at							
A 1		V <sub>CC</sub> -0.6V	3.3V	_	110	_	120	μA	
ΔICC		Data Input = GND or	0.01					μ. ι	
		V <sub>CC</sub> , I <sub>O</sub> = 0A OE Input at							
		VCC							
		Data Input = GND to	0.8V to 3.6V	-	1	—	1	μA	
		3.6V, I <sub>O</sub> = 0A							



## Electrical Characteristics (Cont.)

Symbol	Deremeter	Toot Conditions	N.	T <sub>A</sub> = -40°C	to +125°C	Unit	
Symbol	Parameter	Test Conditions	V <sub>cc</sub>	Min	Max	Unit	
		—	0.8V to 1.65V	0.80 X V <sub>CC</sub>	—		
VIH	High-Level Input	—	1.65V to 1.95V	0.70 X V <sub>CC</sub>	—	v	
VIH	Voltage	—	2.3V to 2.7V	1.6	—	v	
		—	3.0V to 3.6V	2.0	—		
		—	0.8V to 1.65V	—	0.25 X V <sub>CC</sub>		
VIL	Low-Level Input	—	1.65V to 1.95V	—	0.30 X V <sub>CC</sub>	V	
VIL	Voltage	—	2.3V to 2.7V	—	0.7	v	
		_	3.0V to 3.6V	_	0.9		
		I <sub>OH</sub> = -20μA	0.8V to 3.6V	V <sub>CC</sub> – 0.11	—		
		I <sub>OH</sub> = -1.1mA	1.1V	0.6 X V <sub>CC</sub>	—		
		I <sub>OH</sub> = -1.7mA	1.4V	0.93	—		
.,	High-Level Output	I <sub>OH</sub> = -1.9mA	1.65V	1.17	—		
Voh	Voltage	I <sub>OH</sub> = -2.3mA	0.0)/	1.77	—	- V	
		I <sub>OH</sub> = -3.1mA	2.3V	1.67	_		
		I <sub>OH</sub> = -2.7mA	e) /	2.40	_		
		I <sub>OH</sub> = -4mA	3V -	2.30	—		
		I <sub>OL</sub> = 20μΑ	0.8V to 3.6V	_	0.11		
		$I_{OL} = 1.1 \text{mA}$	1.1V	_	0.33 X V <sub>CC</sub>		
		I <sub>OL</sub> = 1.7mA	1.4V	_	0.41		
	Low-Level Output	I <sub>OL</sub> = 1.9mA 1.65V		_	0.39		
V <sub>OL</sub>	Voltage	$I_{OL} = 2.3 \text{mA}$		_	0.36		
		$I_{OL} = 3.1 \text{mA}$	2.3V	_	0.50		
		$I_{OL} = 2.7 \text{mA}$		_	0.36		
		$I_{OL} = 4mA$	3V	_	0.50		
h	Input Current	A or B Input, $V_I = GND$ to 3.6V	0 to 3.6V	_	±0.75	μA	
l <sub>oz</sub>	Z-State Leakage Current	$V_{I}$ or $V_{O} = 0V$ to 3.6V	0 to 3.6V	_	±1.5	μA	
IOFF	Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0	_	±3.5	μA	
$\Delta I_{OFF}$	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2V	—	±2.5	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	—	3.0	μA	
		Data Input at					
		V <sub>CC</sub> –0.6V OE = GND, I <sub>O</sub> =0A	3.3V	—	75	μA	
ΔIcc	ΔI <sub>CC</sub> Additional Supply	OE Input at V <sub>CC</sub> –0.6V Data Input = GND or V <sub>CC</sub> , I <sub>O</sub> =0A	3.3V	_	180	μA	
		OE Input at VCC Data Input = GND to $3.6V$ , $I_O = 0A$	0.8V to 3.6V	-	1	μA	



# **Operating and Package Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Parameter	Test Conditi	-	Vcc	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
~	C <sub>PD</sub> Power Dissipation Capacitance per Gate	f = 1MHz Output Enabled		1.5V ± 0.1V	6.3	~ [
CPD		No Load		1.8V ± 0.15V	6.2	рF
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
CI	Input Capacitance	$V_I = V_{CC} \text{ or } GND$		0V or 3.3V	1.5	pF
		Output Enabled Vo	= GND	0V	2.9	pF
Co	Output Capacitance	Output Disabled V <sub>C</sub> V <sub>CC</sub>	) = GND or	0V or 3.6V	2.1	pF
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8 (Note 9)		_	395	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



# **Switching Characteristics**

### $C_L = 5pF$ see Figure 1

Devenueter	From	То	V		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	11
Parameter	Input	Output	V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V		20.6	—	—			—	
			1.2V ± 0.1V	2.8	5.5	12.6	2.5	14	2.5	17	
	А	Y	1.5V ± 0.1V	2.2	3.9	7.3	2.0	7.6	2.0	8.1	20
t <sub>PD</sub>	A	Ť	1.8V ± 0.15V	1.9	3.2	4.1	1.7	6.1	1.7	6.7	ns
			2.5V ± 0.2V	1.6	2.6	3.6	1.4	4.3	1.4	4.9	
			3.3V ± 0.3V	1.4	2.4	3.1	1.2	3.9	1.2	4.4	
		Y	0.8V	_	71.6	_	—	—	_	—	- - ns
			1.2V ± 0.1V	2.8	6.2	14.9	2.6	19.6	2.6	19.8	
4			1.5V ± 0.1V	2.3	4.2	8.3	2.2	8.8	2.2	9.2	
t <sub>EN</sub>	ŌE		1.8V ± 0.15V	1.9	3.3	6.4	1.7	7.1	1.7	7.4	
			2.5V ± 0.2V	1.5	2.4	4.3	1.4	4.6	1.4	4.9	
			3.3V ± 0.3V	1.3	2.0	3.8	1.2	4.2	1.2	4.4	
			0.8V	_	10.3		_	_	_	—	
			1.2V ± 0.1V	2.6	4.2	8.9	2.9	9.2	2.9	9.4	
	ŌĒ	Y	1.5V ± 0.1V	2.1	3.2	6.4	2.2	6.6	2.2	6.7	20
t <sub>DIS</sub>	ÛE	ř	1.8V ± 0.15V	2.1	3.1	5.6	1.7	5.8	1.7	6.1	ns
			2.5V ± 0.2V	1.7	2.4	4.0	1.4	4.3	1.4	4.5	
			3.3V ± 0.3V	2.1	2.8	4.9	1.2	5.0	1.2	5.1	

### $C_L = 10 pF$ see Figure 1

Parameter	From	То	N		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Parameter	Input	Output	V <sub>cc</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	24.0	_	_	—	_	—	
		1.2V ± 0.1V	3.2	6.4	14.8	3.0	16.6	3.0	18.3		
4	А	Y	1.5V ± 0.1V	2.1	4.5	8.8	1.9	9.1	1.9	9.4	20
t <sub>PD</sub>	A	Ť	1.8V ± 0.15V	1.9	3.8	5.5	1.7	6.8	1.7	7.6	ns
			2.5V ± 0.2V	2.1	3.2	4.2	1.6	5.3	1.6	5.9	
			3.3V ± 0.3V	1.8	3.0	3.8	1.6	4.6	1.6	5.2	
		· Y	0.8V	_	75.3	_	_	—	_	—	
			1.2V ± 0.1V	3.2	7.1	16.9	3.0	22.2	3.0	22.4	
	OE		1.5V ± 0.1V	2.2	4.8	9.6	2.1	10.0	2.1	10.3	20
t <sub>EN</sub>	OE	Ť	1.8V ± 0.15V	1.8	3.9	7.1	1.7	7.8	1.7	8.2	ns
			2.5V ± 0.2V	1.5	2.9	5.0	1.4	5.4	1.4	5.8	
			3.3V ± 0.3V	1.4	2.6	4.7	1.3	4.9	1.3	5.2	
			0.8V	_	12.2	_	_	—	_	—	
			1.2V ± 0.1V	3.5	5.3	10.9	3.3	11.4	3.3	11.6	
1		Y	1.5V ± 0.1V	2.2	4.1	8.0	2.1	8.2	2.1	8.5	20
tDIS	OE	Ť	1.8V ± 0.15V	2.4	4.2	7.1	1.7	7.4	1.7	7.6	ns
			2.5V ± 0.2V	1.9	3.2	5.1	1.4	5.5	1.4	5.7	
			3.3V ± 0.3V	2.4	4.1	6.8	1.3	7.1	1.3	7.2	



# Switching Characteristics (Cont.)

### $C_L = 15 pF$ see Figure 1

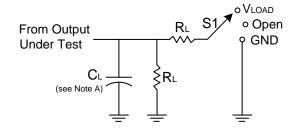
Deremeter	From	То	N N		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit	
Parameter	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	Onit	
			0.8V	_	27.4	—	—	—	_	—		
			1.2V ± 0.1V	3.6	7.2	15.5	3.3	22.4	3.3	22.5		
	٨	Y	1.5V ± 0.1V	3.0	5.1	8.8	2.5	9.8	2.5	10.9		
tPD	A	ř	1.8V ± 0.15V	2.2	4.3	6.3	2.0	7.9	2.0	8.8	ns	
			2.5V ± 0.2V	2.0	3.7	4.9	1.8	6.0	1.8	6.7		
			3.3V ± 0.3V	2.0	3.5	4.4	1.8	5.4	1.8	6.1		
		Y	0.8V	_	79.2	_	_	—		—	ns	
			1.2V ± 0.1V	3.6	7.8	19.0	3.3	21.8	3.3	22		
			1.5V ± 0.1V	3.0	5.4	10.6	2.9	11.3	2.9	11.6		
t <sub>EN</sub>	OE		1.8V ± 0.15V	2.1	4.3	8.0	2.0	8.8	2.0	9.2		
			2.5V ± 0.2V	1.8	3.4	5.8	1.7	6.2	1.7	6.7		
			3.3V ± 0.3V	1.6	3.1	5.3	1.5	5.9	1.5	6.1		
			0.8V	_	14.9	_	_	—	_	—		
			1.2V ± 0.1V	4.3	6.4	13.9	3.7	15.5	3.7	15.7		
		V	1.5V ± 0.1V	3.0	5.0	8.8	2.5	9.7	2.5	9.9	-	
t <sub>DIS</sub> OE	OE	OE Y	1.8V ± 0.15V	3.1	5.4	8.8	2.0	10.3	2.0	10.5	ns	
			2.5V ± 0.2V	2.4	4.0	8.2	1.7	8.4	1.7	8.6		
			3.3V ± 0.3V	3.2	5.3	8.6	1.5	9.2	1.5	9.4		

### $C_L = 30 pF$ see Figure 1

Deremeter	From	То	V		T <sub>A</sub> = +25°C	;	T <sub>A</sub> = -40°C	C to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit	
Parameter	Input	Output	V <sub>cc</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit	
			0.8V	_	37.4	_	_		_	_		
		1.2V ± 0.1V	4.8	9.5	20.7	4.4	27.6	4.4	27.8			
	А	Y	1.5V ± 0.1V	4.0	6.7	10.8	3.0	13.0	3.0	14.5	20	
t <sub>PD</sub>	A	ř	1.8V ± 0.15V	2.9	5.6	8.4	2.6	10.3	2.6	11.5	ns	
			2.5V ± 0.2V	2.7	4.8	6.3	2.5	7.8	2.5	8.7		
			3.3V ± 0.3V	2.7	4.6	5.8	2.5	7.0	2.5	8.3		
			0.8V	_	90.6	_	_	_	_	—	ns	
		Y	1.2V ± 0.1V	4.7	10.0	24.5	4.3	26.4	4.3	26.6		
			1.5V ± 0.1V	3.0	6.9	13.6	3.7	14.4	3.7	15.0		
t <sub>EN</sub>	OE		1.8V ± 0.15V	2.6	5.6	10.3	3.2	11.4	3.2	12.1		
			2.5V ± 0.2V	2.3	4.5	7.6	2.9	8.2	2.9	8.8		
			3.3V ± 0.3V	2.2	4.2	7.5	2.7	8.3	2.7	8.7		
			0.8V	_	51.6	—	—	—	_	—		
			1.2V ± 0.1V	6.0	9.8	16.3	4.7	18.7	4.7	18.9		
	OE	Y	1.5V ± 0.1V	4.5	7.7	12.6	3.0	12.8	3.0	13.2	20	
tDIS	OE	ř	1.8V ± 0.15V	5.2	8.8	13.7	2.6	13.8	2.6	13.9	ns	
			2.5V ± 0.2V	3.9	6.4	8.9	2.3	10.8	2.3	12.2		
			$3.3V \pm 0.3V$	5.5	9.0	13.9	2.2	14.0	2.2	15.6		

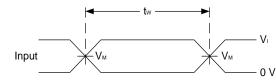


### **Parameter Measurement Information**

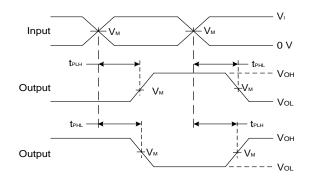


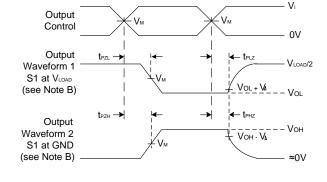
TEST	S1	RL
t <sub>PLH</sub> /t <sub>PHL</sub>	Open	1MΩ
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>	5ΚΩ
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND	5ΚΩ

N N	Inj	outs	V <sub>M</sub>	VLOAD	CL	νΔ
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>				
0.8V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.1V
1.2V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.5V±0.1V	Vcc	≤3ns	V <sub>CC</sub> /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.1V
1.8V±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.15V
2.5V±0.2V	Vcc	≤3ns	V <sub>CC</sub> /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.15V
3.3V±0.3V	Vcc	≤3ns	V <sub>CC</sub> /2	$2 X V_{CC}$	5, 10, 15, 30pF	0.3V











#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

### Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate  $\leq$  10MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{\mathsf{PLZ}}$  and  $t_{\mathsf{PHZ}}$  are the same as  $t_{\mathsf{DIS.}}$
- E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN}}$
- F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



### X2-DFN1210-8

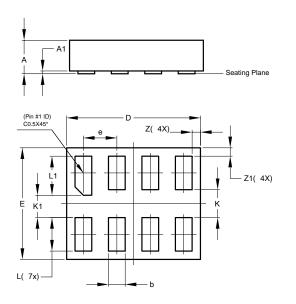


X : Week : A~Z : Internal Code

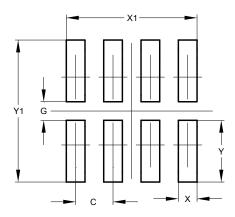
Part Number	Package	Identification Code	
74AUP2G126RA3-7	X2-DFN1210-8	KT	

## X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1210-8				
Dim	Min	Мах	Тур	
Α	-	0.35	0.30	
A1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
Е	0.95	1.05	1.00	
е	-	-	0.30	
K	-	-	0.25	
K1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z1	0.050	0.100	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Y	0.500
Y1	1.150



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